Elektronische Bauelemente

SSU10N65H-C

10.2A, 650V, $R_{DS(ON)}$ 0.65Ω
N-Channel Super Junction Power MOSFET

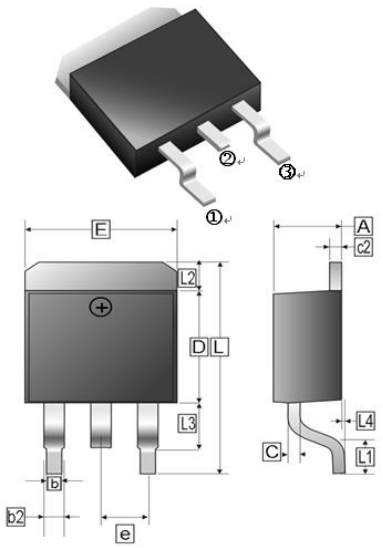
RoHS Compliant Product
A suffix of "-C" specifies halogen free

DESCRIPTION

The SSU10N65H-C is power MOSFET using Super Junction Technology that can realize very low on-resistance and gate charge. It will provide much high efficiency by using optimized charge coupling technology. These user friendly devices give an advantage of low EMI to designers as well as low switching loss, which provide excellent $R_{DS(ON)}$ and gate charge for most of the synchronous buck converter applications.

The SSU10N65H-C meet the RoHS and Green Product requirement with full function reliability approved.

TO-263



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.00	4.87	c2	1.07	1.65
b	0.51	1.01	b2	1.34 REF	
L4	0.00	0.30	D	8.0	9.65
C	0.30	0.74	e	2.54 REF	
L3	1.50 REF		L	14.6	16.1
L1	2.5 REF		L2	1.27 REF	
E	9.60	10.67			

FEATURES

- Advanced Super Junction Technology
- Super Low Gate Charge
- Green Device Available

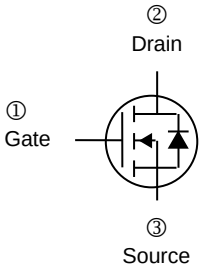
MARKING

PACKAGE INFORMATION

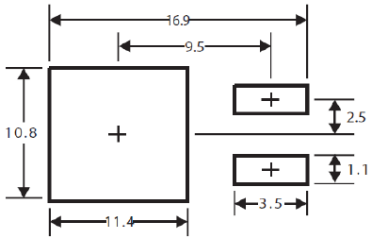
Package	MPQ	Leader Size
TO-263	0.8K	13 inch

ORDER INFORMATION

Part Number	Type
SSU10N65H-C	Lead (Pb)-free and Halogen-free



Mounting Pad Layout



*Dimensions in millimeters

ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise specified)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	650	V
Gate-Source Voltage		V_{GS}	±30	V
Continuous Drain Current [1,4] @V_{GS}=10V	T_C=25°C	I_D	10.2	A
	T_C=100°C		6.5	
Pulsed Drain Current [2]		I_{DM}	40	A
Power Dissipation	T_C=25°C	P_D	100.8	W
Operating Junction and Storage Temperature		T_J, T_{STG}	-55~150	°C
Thermal Resistance Rating				
Thermal Resistance Junction-Ambient [1]		$R_{\theta JA}$	62.5	°C/W
Thermal Resistance Junction-Case [1]		$R_{\theta JC}$	1.24	

ELECTRICAL CHARACTERISTICS (T_J=25°C unless otherwise specified)

Parameter		Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain-Source Breakdown Voltage		$V_{(BR)DSS}$	650	-	-	V	V_{GS}=0V, I_D=250μA
Gate-Threshold Voltage		$V_{GS(th)}$	2	-	4	V	V_{DS}=V_{GS}, I_D=250μA
Gate-Source Leakage Current		I_{GSS}	-	-	±100	nA	V_{GS}= ±30V
Drain-Source Leakage Current	T_J=25°C	I_{DSS}	-	-	1	μA	V_{DS}=520V, V_{GS}=0V
	T_J=55°C		-	-	5		
Static Drain-Source On-Resistance [3]		$R_{DS(ON)}$	-	0.54	0.65	Ω	V_{GS}=10V, I_D=2.1A
Total Gate Charge		Q_g	-	13.8	-	nC	I_D=7.3A V_{DS}=520V V_{GS}=10V
Gate-Source Charge		Q_{gs}	-	3.6	-		
Gate-Drain Change		Q_{gd}	-	5.6	-		
Turn-on Delay Time		$T_{d(on)}$	-	18	-	nS	V_{DS}=325V I_D=7.3A V_{GS}=10V R_G=25Ω
Rise Time		T_r	-	33	-		
Turn-off Delay Time		$T_{d(off)}$	-	80	-		
Fall Time		T_f	-	28	-		
Input Capacitance		C_{iss}	-	545	-	pF	V_{GS}=0V V_{DS}=25V f=1MHz
Output Capacitance		C_{oss}	-	640	-		
Reverse Transfer Capacitance		C_{rss}	-	28.6	-		
Source-Drain Diode							
Diode Forward Voltage [2]		V_{SD}	-	-	1.4	V	I_S=7.3A, V_{GS}=0V
Continuous Source Current [1,4]		I_S	-	-	10.2	A	V_G=V_D=0, Force Current
Pulsed Source Current [2]		I_{SM}	-	-	40	A	
Reverse Recovery Time		T_{rr}	-	272	-	nS	V_{DD}=100V, I_S=7.3A, dI/dt=100A/μs
Reverse Recovery Charge		Q_{rr}	-	3	-	μC	

Notes:
1. Surface mounted on a 1 inch^2 FR-4 board with 2oz copper.
2. Pulse width limited by maximum junction temperature, pulse width≦10us, duty cycle≦2%.
3. The data tested by pulsed, pulse width≦300us, duty cycle≦2%.
4. Silicon limitation current is 7.3A

CHARACTERISTIC CURVES

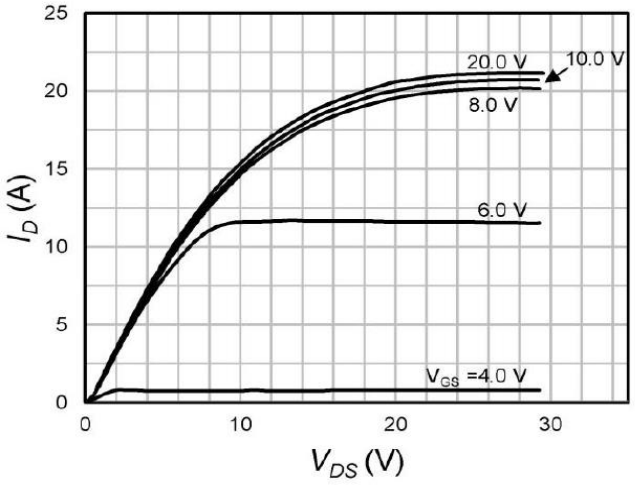


Fig.1 Typical Output Characteristics

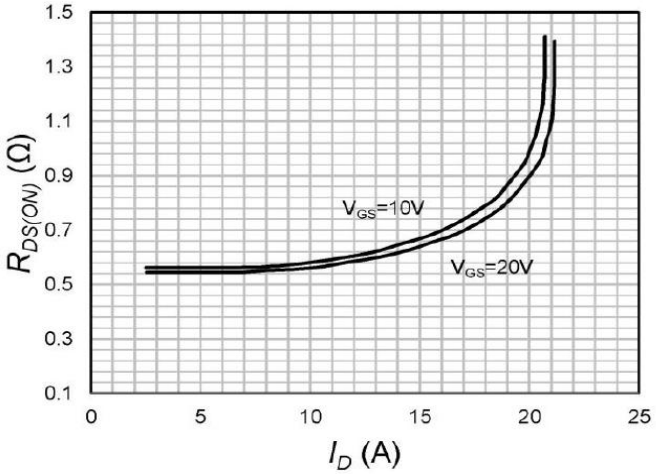


Fig.2 On-Resistance vs. Drain Current

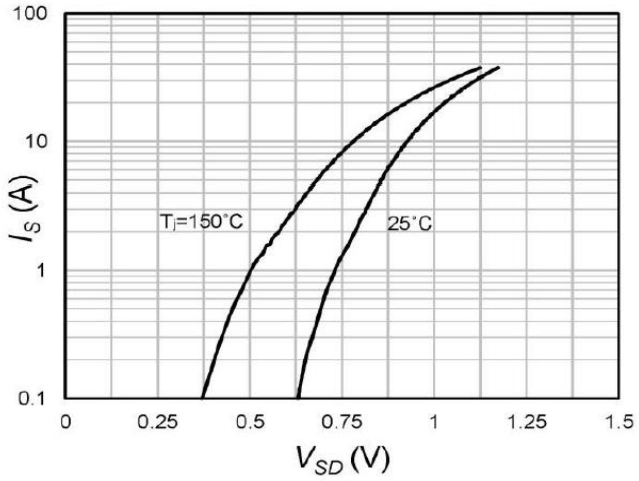


Fig.3 Forward Characteristics of Reverse

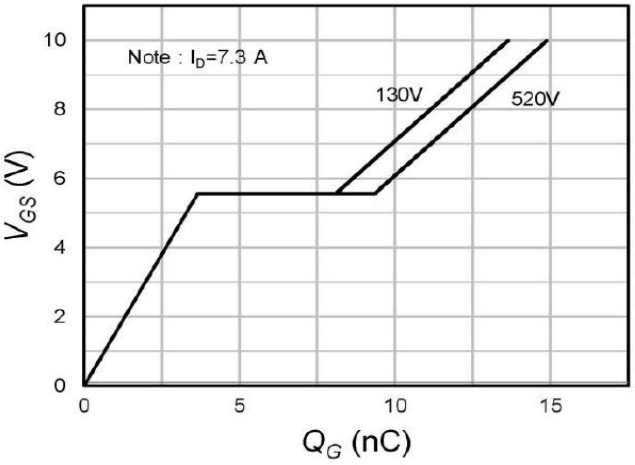


Fig.4 Gate-Charge Characteristics

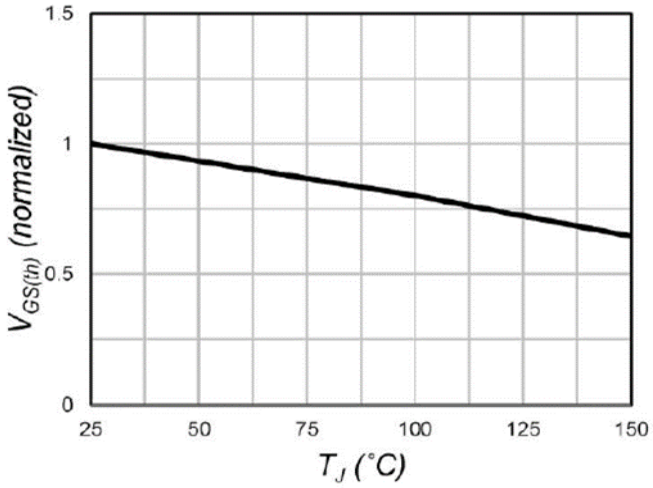


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

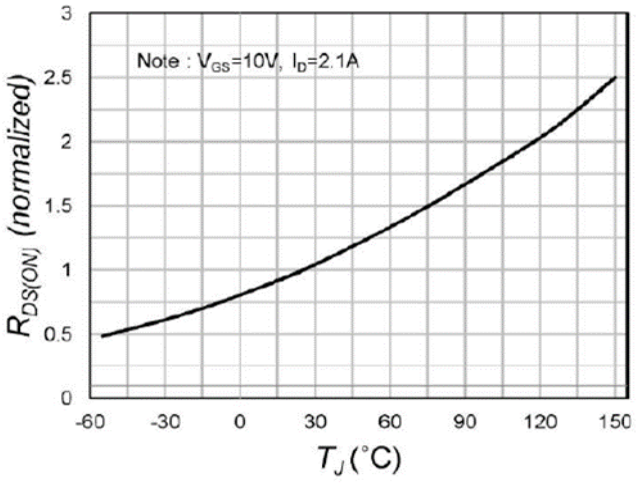


Fig.6 Normalized R_{DSON} vs. T_J

CHARACTERISTIC CURVES

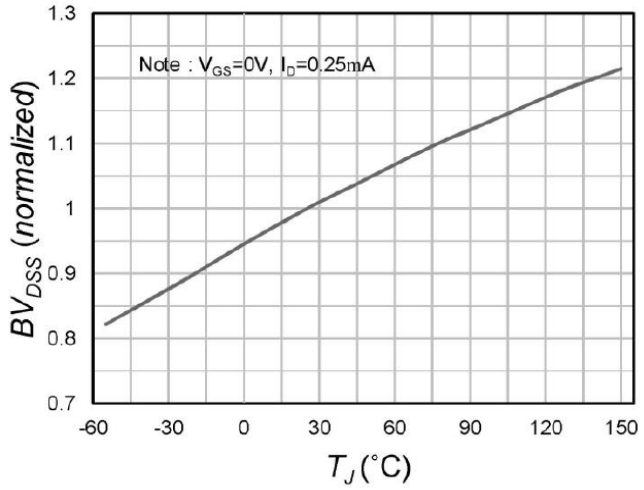


Fig.7 Drain-Source Breakdown Voltage(Normaized)

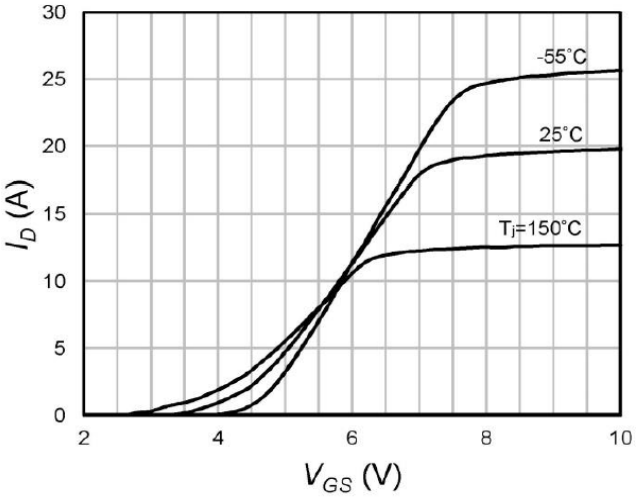


Fig.8 Transfer Characteristics

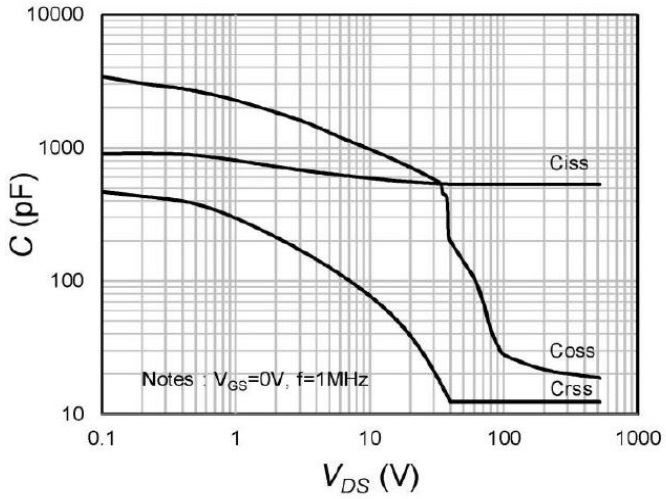


Fig.9 Capacitances

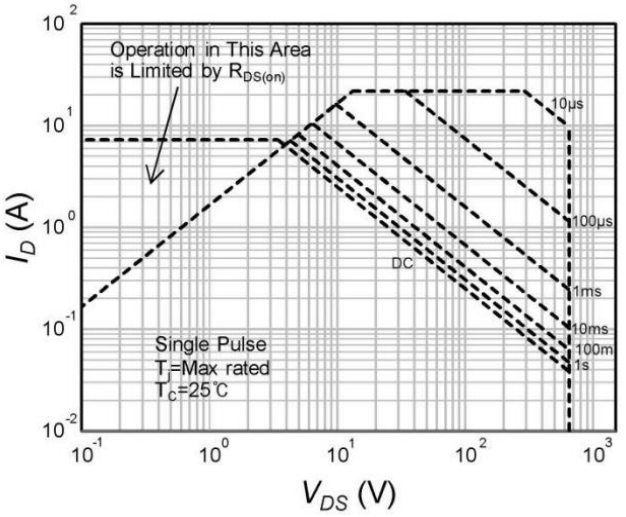


Fig.10 Safe Operating Area

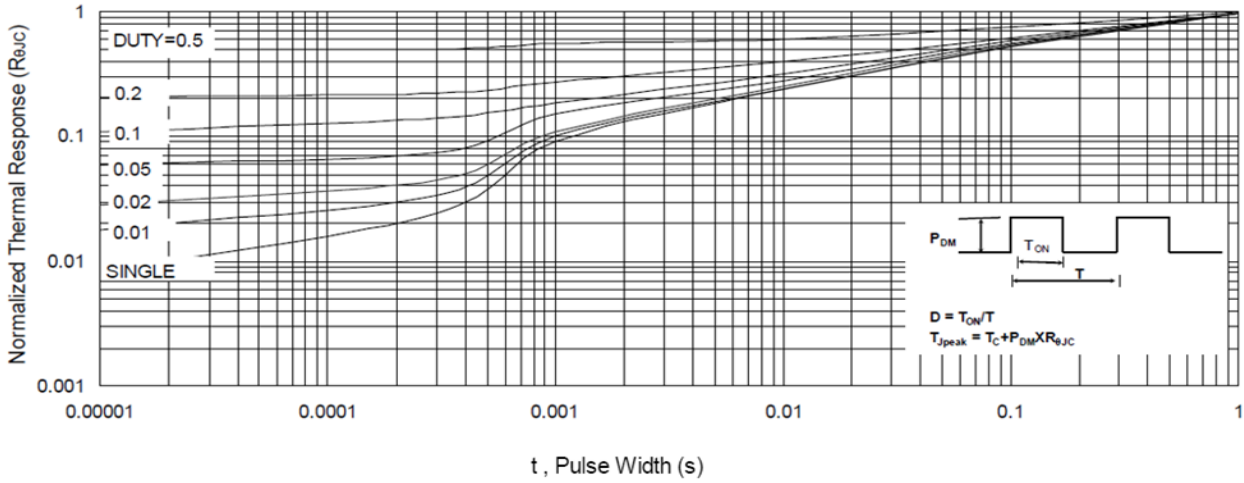


Fig.11 Normalized Maximum Transient Thermal Impedance